



APR347

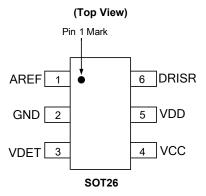
SECONDARY SIDE SYNCHRONOUS RECTIFICATION CONTROLLER

Description

The APR347 is a secondary side MOSFET driver for synchronous rectification in DCM operation.

The synchronous rectification can effectively reduce the secondary side rectifier power dissipation and provide high performance solution. By sensing primary MOSFET gate-to-source voltage, the APR347 can output ideal drive signal with less external components. The APR347 is available in the SOT26 package.

Pin Assignments



Features

- Synchronous Rectification for DCM Operation Flyback
- Eliminate Resonant Ring Interference
- Fewest External Components
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

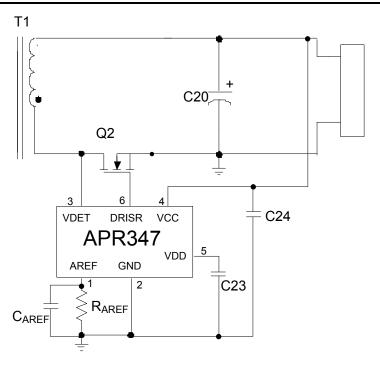
Applications

 Adapters/Chargers for Cell/Cordless Phones, ADSL Modems, MP3 and Other Portable Apparatus

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Typical Applications Circuit

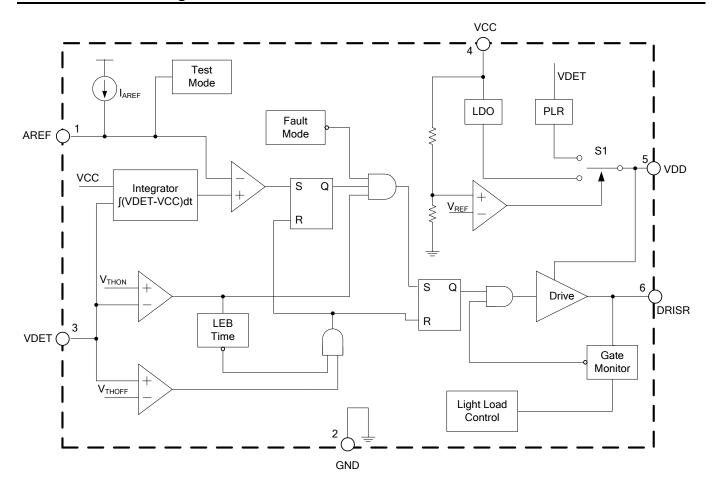




Pin Descriptions

Pin Number	Pin Name	Function
1	AREF	Program a voltage reference with a resistor from AREF to GND, to enable synchronous rectification MOSFET drive signal
2	GND	Ground
3	VDET	SR MOS drain-to-source voltage sense input, connected to drain pin of SR MOSFET through a resistor
4	VCC	Power supply, connected with system output Input of internal LDO and system output voltage sensing circuit.
5	VDD	Internal power supply. It provides bias voltage for the internal logic circuit and the MOSFET driver. Connect this pin to a capacitor.
6	DRISR	Synchronous rectification MOSFET Gate drive

Functional Block Diagram





Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Rating	Unit
V _{CC} Supply Voltage		-0.3 to 28	V
V_{DET}	Voltage at VDET Pin (Note 5)	-0.7 to 150	V
V _{DRISR}	Voltage at DRISR Pin	-0.3 to 7	V
V_{DD}	Internal Power Supply Voltage	-0.3 to 7.5	V
P _D	Power Dissipation at T _A = +25°C	0.6	W
TJ	Operating Junction Temperature	+150	°C
T _{STG}	Storage Temperature	-65 to +150	°C
T _{LEAD} Lead Temperature (Soldering, 10s)		+300	°C
θ _{JA} Thermal Resistance (Junction to Ambient)		197	°C/W
θ _{JC}	Thermal Resistance (Junction to Case)	76	°C/W

Notes:

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	0	22	V
T _A	Ambient Temperature	-40	+85	°C

^{4.} Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied.

Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

5. VDET pin is ESD sensitive and passes 1000V HBM. The JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process. The aging condition of VDET pin is 80% of AMR value.



$\textbf{Electrical Characteristics} \ (\textcircled{@} \ V_{CC} = 5V, \ T_A = -40^{\circ}C \ < T_A < +85^{\circ}C, \ unless \ otherwise \ specified.)$

Symbol	Parameter	Condition	Min	Тур	Max	Unit	
Supply Voltage (VCC Pin)							
ISTARTUP	Startup Current	V _{CC} = V _{STARTUP} -0.1V	-	150	_	μA	
I _{OP}	Operating Current	VDET Pin Floating V _{CC} = 5V	_	150	_	μA	
VSTARTUP	Startup Voltage	_	_	2.4	_	V	
-	UVLO	_	_	2.2	_	V	
V _{DD_ENABLE}	VDD Enable Falling Threshold at VCC Pin	_	_	4.6	_	V	
V _{DD_DISABLE}	VDD Disable Rising Threshold at VCC Pin	-	_	4.75	_	V	
V _{DD_HYS}	VDD Disable Hysteresis at VIN Pin	_	_	150	_	mV	
VDD Pin							
V_{DD}	Internal Power Supply Voltage	_	_	5.5	_	V	
Gate Driver							
V _{THON}	Gate Turn On Threshold	-	0	_	1	V	
V_{THOFF}	Gate Turn Off Threshold	_	-	-5	_	mV	
t _{DON}	Turn On Delay Time	From V _{THON} to V _{DRISR} = 1V	-	70	180	ns	
t _{DOFF}	Turn Off Propagation Delay Time	From V _{THOFF} to V _{DRISR} = 4V	_	100	150	ns	
t _{RG}	Turn On Rising Time	From 1V to 4V, V _{CC} =5V, C _L =4.7nF	-	50	100	ns	
t _{FG}	Turn Off Falling Time	From 4V to 1V, V _{CC} =5V, C _L =4.7nF	_	20	100	ns	
t _{ON_MIN}	Minimum On Time	-	1.2	1.6	2	μs	
toff_min	Minimum Off Time	-	-	2	_	μs	
		V _{CC} <4.6V	_	-	V _{DD} -0.1		
V _{DRISR}	SR Drive Voltage	V _{CC} >4.75V	_	_	V _{CC} -0.1		
K _{QS}	(Note 6)	-	_	0.42	_	mA*µs	
V _{S_MIN}	Synchronous Rectification (SR) Minimum Operating Voltage (Note 7)	-	_	_	4.5	V	
Green Mode (Note 8)							
t_LL	Minimum Off Time to Enter Green Mode	_	_	600	_	μs	

Notes:

- 6. This item is used to specify the value of R_{AREF}.
 7. This item specifies the minimum SR operating voltage of V_{IN_DC}, V_{IN_DC}≥N_{PS}*V_{S_MIN}.
 8. These parameters are guaranteed by design and characterization.



Synchronous Rectification Principle Description

SR MOSFET Turn on

The APR347 determines the synchronous rectification MOSFET turn-on time by monitoring the MOSFET drain-to-source voltage. When the drain voltage is lower than the turn-on threshold voltage V_{THON}, the IC outputs a positive drive voltage after a turn-on delay time (t_{DON}). The MOSFET will turn on and the current will transfer from the body diode into the MOSFET's channel. Because of the parasitic parameter, the voltage on the MOSFET drain pin may have a moderate voltage ringing at this moment, which may impact the VDET voltage and result in a turning-off fault. To avoid this fault situation happening, a Minimum On-Time (t_{ONMIN}) blanking period is used to maintain the power MOSFET on for a minimum amount of time.

In Figure 1, the turn-on blanking time tonmin is to prevent the MOSFET drain-to-source voltage ringing effect.

Turn off Operation

The DCM operation of the SR is described with the timing diagram shown in Figure 1.

In the process of the drain current decreasing linearly toward zero, the drain-source voltage rises synchronically. When it rises over the turn-off threshold voltage V_{THOFF}, the APR347 pulls the drive signal down after a turn-off delay (t_{DOFF}).

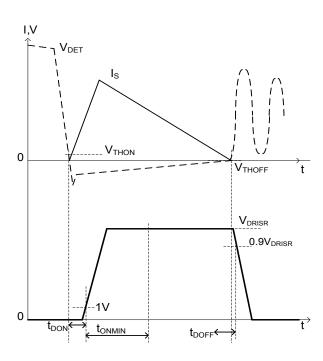


Figure 1. Typical Waveforms of APR347 in DCM

Minimum On/Off Time

When the controlled MOSFET gate is turned on, some ringing noise is generated. The minimum on-time timer blanks the V_{THOFF} comparator, keeping the controlled MOSFET on for at least the minimum on time. During the minimum on time, the turn off threshold is totally blanked.

After the SR driver turns off, the SR control block initiates a minimum off-time timer, during which the SR will remain off to avoid the ringing from turning on the synchronous MOSFET.



Synchronous Rectification Principle Description (continued)

The Value and Meaning of AREF Resistor

As to the DCM operation flyback converter—after the secondary rectifier stops conducting, the resonance of the primary inductance and output capacitance of the equivalent switch device creates the primary MOSFET drain-to-source ringing waveform. This ringing waveform may lead to Synchronous Rectifier error conduction. To avoid this fault occurance, the APR347 has a special function by means of volt-second product detecting. Regarding the sensed voltage of the VDET pin, the volt-second product of a voltage above V_{CC} at primary switch on-time is much higher than that of each cycle ringing voltage above V_{CC} . Therefore, before each time the Synchronous Rectifier turns on, the APR347 judges if the detected volt-second product of the VDET voltage above V_{CC} is higher than a threshold, and then turns on the Synchronous Rectifier. The purpose of the AREF resistor is to calculate the volt-second product threshold. The APR347 has a parameter, Kqs, which converts the R_{AREF} value to the volt-second product.

$$Area2 = R_{AREF} * Kqs$$

In general, the Area1 and Area3 values depend on the system design and are always fixed if the system design is frozen. As to Diodes' PSR design, the Area1 value changes with primary peak current value and Area3 value generally keeps constant in all conditions. So the AREF resistor design should consider the worst case scenario and the minimum primary peak current condition. Because of the distribution of the system design parameters, Area1 and Area3 may have moderate tolerance. So Area2 should be designed in the middle of Area1 and Area3 to ensure enough design margins.

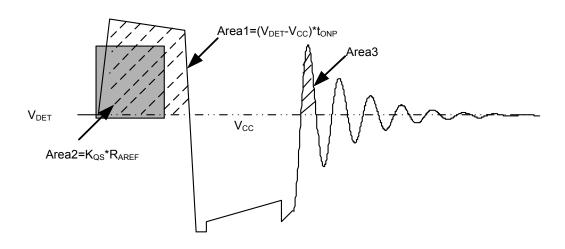


Figure 2. AREF Function

SR Minimum Operating Voltage

The APR347 sets a minimum SR operating voltage by comparing the difference between V_{DET} and the output voltage (V_{CC}). When the value of V_{DET} – V_{CC} is higher than its internal reference, the APR347 will begin to integrate the area of (V_{DET} – V_{CC})* t_{ONP} . If not, the area integrating will not begin and the SR driver will be disabled.

Recommended Application Circuit Parameters

The C_{AREF} is recommended to be parallel with the AREF resistor to keep the volt-second product threshold stable. The recommended value of the C_{AREF} is 20nF. The recommended value of the C24 is 100nF. The value of the V_{DD} capacitor C23 is 4.7 μ F.

Green Mode at Light Load

When the system is running with light load, rectifier conduction loss no longer dominates the secondary-side power loss. In this condition, it is recommended that the SR MOSFET stays off to save from driver loss.

The APR347 will sense the non-switching duration cycle-by-cycle. When the non-switching duration remains longer than the internal light load timing t_{LL} , the IC will shut down the gate driver, which will stay off for the next two cycles.



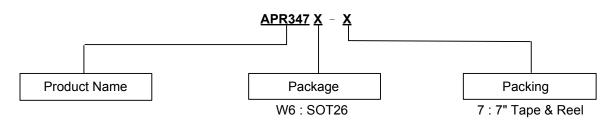
Synchronous Rectification Principle Description (continued)

 V_{DD}

The V_{DD} is the output voltage of the Pulse Linear Regulator (PLR) or the Low Dropout Regulator (LDO). It provides bias voltage for the controller. A capacitor (typically 4.7μF) should be connected between the VDD pin and GND pin.

A Pulse Linear Regulator is integrated in the controller to provide voltage to the VDD pin of the APR347. With the PLR, the APR347 can operate at a low voltage output condition, in which the system output voltage may drop to as low as 2V. The bias voltage will change from the PLR to the LDO when the system output voltage is higher than 4.75V. In this case, the system output provides voltage to the APR347's VDD through the internal LDO.

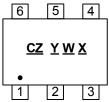
Ordering Information



Ī					7"Tape and Reel		
	Package	Temperature Range	Part Number	Marking ID	Quantity	Part Number Suffix	
	SOT26	-40°C to +85°C	APR347W6-7	CZ	3000/Tape and Reel	-7	

Marking Information





XX: Identification Code

Y : Year 0~9

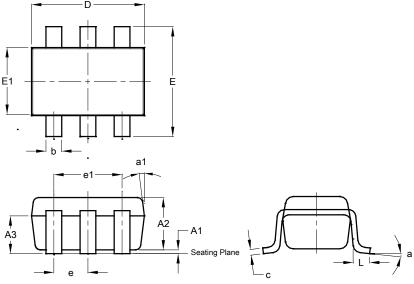
____ <u>W</u> : Week : A~Z : 1~26 week; a~z : 27~52 week; z represents 52 and 53 week

X: Internal Code



Package Outline Dimensions (All dimensions in mm (inch).)

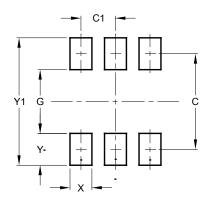
SOT26 (SC74R)



SOT26 (SC74R)				
Dim	Min	Max	Тур	
A1	0.013	0.10	0.05	
A2	1.00	1.30	1.10	
A3	0.70	0.80	0.75	
b	0.35	0.50	0.38	
С	0.10	0.20	0.15	
D 2.90		3.10	3.00	
е -		-	0.95	
e1	-	-	1.90	
Е	2.70	3.00	2.80	
E1	1.60			
L	0.35	0.55	0.40	
а	-	-	8°	
a1 7°				
All Dimensions in mm				

Suggested Pad Layout

SOT26 (SC74R)



Dimensions	Value (in mm)		
С	2.40		
C1	0.95		
G	1.60		
Х	0.55		
Y	0.80		
V1	3 20		

Mechanical Data

- Moisture Sensitivity: MSL Level 1 per JESD22-A113
- Terminals: Finish Matte Tin Plated Leads, Solderable per JESD22-B102 @3
- Weight: 0.016 grams (Approximate)



IMPORTANT NOTICE

- 1. DIODES INCORPORATED AND ITS SUBSIDIARIES ("DIODES") MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes products. Diodes products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of the Diodes products for their intended applications, (c) ensuring their applications, which incorporate Diodes products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

Copyright © 2020 Diodes Incorporated

www.diodes.com